

PSMN8R7-80PS

N-channel 80 V 8.7 m Ω standard level MOSFET in TO-220

Rev. 02 — 1 November 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
-					אני		
V _{DS}	drain-source voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$		-	-	80	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>		-	-	90	Α
P_{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2		-	-	170	W
T _j	junction temperature			-55	-	175	°C
Static char	racteristics						
DOON	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{ or } 12}$		-	-	14	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{}$	[1]	-	7.5	8.7	mΩ
Dynamic o	haracteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$		-	11	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 40 V; see <u>Figure 14</u> ; see <u>Figure 15</u>		-	52	-	nC
Avalanche	ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} &V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C;} \\ &I_D = 90 \text{ A; } V_{sup} \leq 80 \text{ V;} \\ &R_{GS} = 50 \Omega; \text{ unclamped} \end{split}$		-	-	120	mJ

^[1] Measured 3 mm from package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		_G (EA)
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN8R7-80PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	80	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	80	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	64	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	-	90	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3	-	361	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	170	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	-	90	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	361	Α
Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 90 A; $V_{sup} \le$ 80 V; R_{GS} = 50 Ω ; unclamped	-	120	mJ

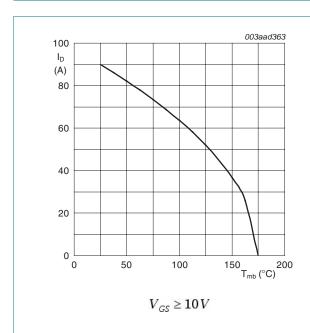


Fig 1. Continuous drain current as a function of mounting base temperature

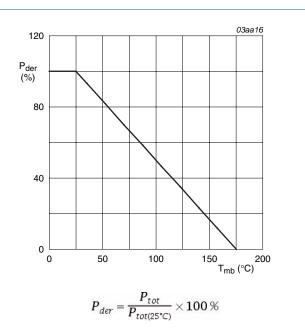
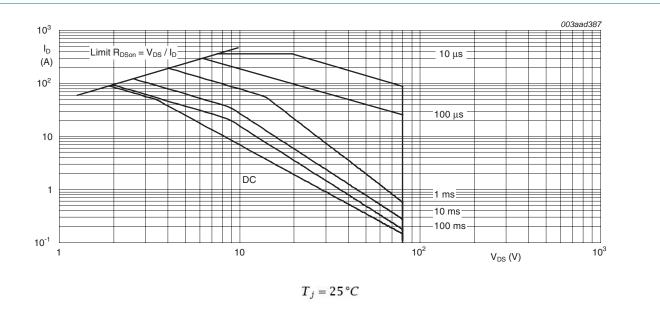


Fig 2. Normalized total power dissipation as a function of mounting base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.54	0.88	K/W

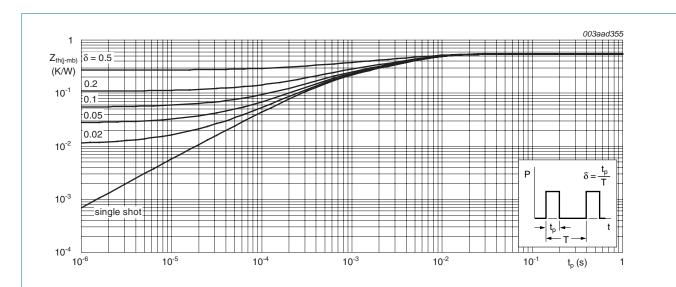


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	73	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V
V _{GS(th)} ga	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 10	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	4.6	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 11</u> ; see <u>Figure 10</u>	2.3	3	4	V
I _{DSS}	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.3	5	μΑ
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μΑ
I _{GSS} ga	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nΑ
R _{DSon} drain-source or	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 175 \text{ °C};$ see <u>Figure 12</u>	-	-	20.8 8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	-	14	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	[1] -	7.5	8.7	mΩ	
R_G	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic o	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	44	-	nC
		$I_D = 25 \text{ A}$; $V_{DS} = 40 \text{ V}$; $V_{GS} = 10 \text{ V}$;	-	52	-	nC
Q_{GS}	gate-source charge	see Figure 14; see Figure 15	-	15	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 25 \text{ A}$; $V_{DS} = 40 \text{ V}$; $V_{GS} = 10 \text{ V}$;	-	9.2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge	see <u>Figure 14</u>	-	5.8	-	nC
Q_{GD}	gate-drain charge	$I_D = 25 \text{ A}$; $V_{DS} = 40 \text{ V}$; $V_{GS} = 10 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	11	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}$; $V_{DS} = 40 \text{ V}$; see <u>Figure 15</u>	-	4.6	-	V
C _{iss}	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	3346	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	296	-	pF
C _{rss}	reverse transfer capacitance		-	158	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 1.6 \Omega; V_{GS} = 10 \text{ V};$	-	21	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	26	-	ns
$t_{d(off)}$	turn-off delay time		-	46	-	ns
t _f	fall time		-	20	-	ns
Source-dra	ain diode					
V_{SD}	source-drain voltage	$I_S = 10 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.79	1.2	V

 Table 6.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s};$	-	42	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 40 \text{ V}$	-	66	-	nC

[1] Measured 3 mm from package.

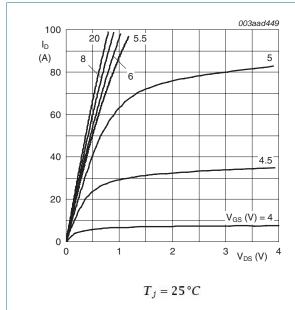


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

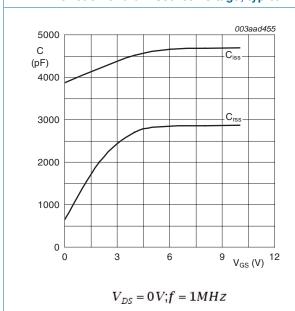


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

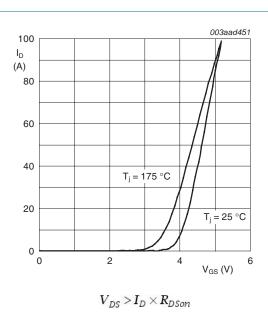


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

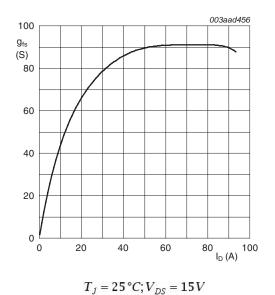
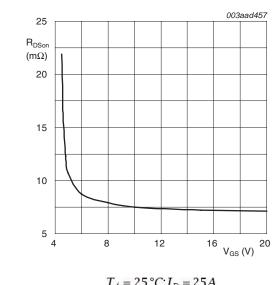


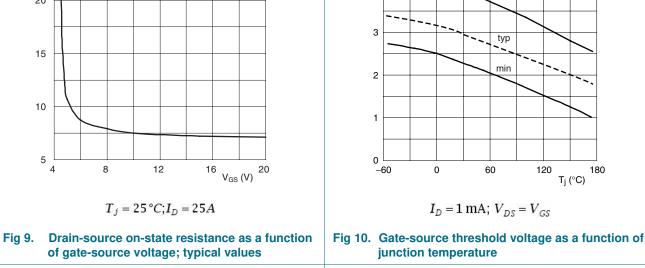
Fig 8. Forward transconductance as a function of drain current; typical values

PSMN8R7-80PS

max



of gate-source voltage; typical values



5 V_{GS(th)} (V)

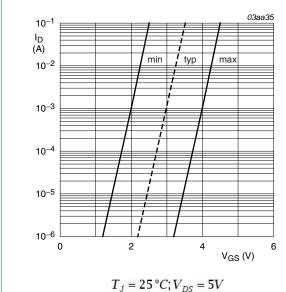


Fig 11. Sub-threshold drain current as a function of gate-source voltage

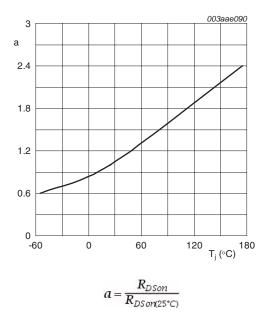
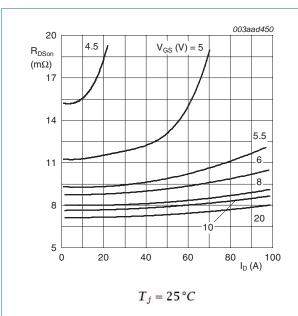


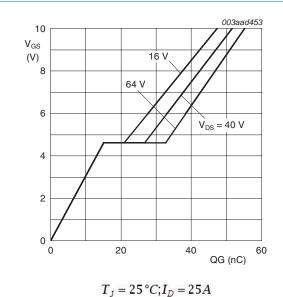
Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



V_{GS}(pl)
V_{GS}(th)
V_{GS}
Q_{GS1} Q_{GS2}
Q_{GS}
Q_G(tot)
003aaa508

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

Fig 14. Gate charge waveform definitions



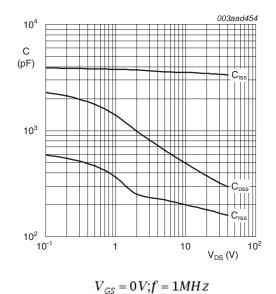


Fig 15. Gate-source voltage as a function of gate charge; typical values



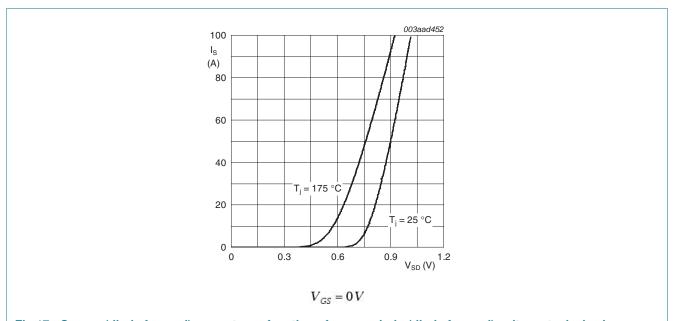
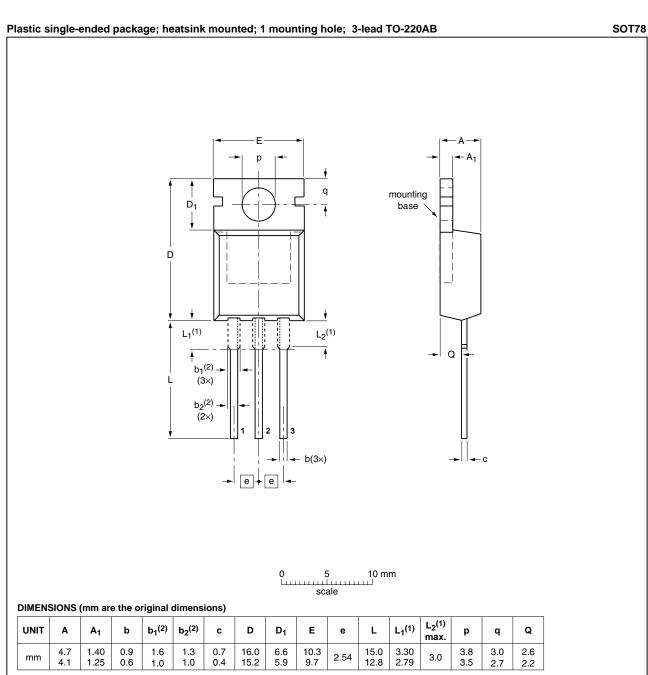


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline



Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig 18. Package outline SOT78 (TO-220AB)

PSMN8R7-80PS

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN8R7-80PS v.2	20101101	Product data sheet	-	PSMN8R7-80PS v.1
Modifications:Status changed from objective to product.Various changes to content.				
PSMN8R7-80PS v.1	20100129	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PSMN8R7-80PS

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11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information
4	Limiting values
5	Thermal characteristics5
6	Characteristics6
7	Package outline
8	Revision history12
9	Legal information13
9.1	Data sheet status
9.2	Definitions13
9.3	Disclaimers
9.4	Trademarks14
10	Contact information 1/